



## MM54HC10/MM74HC10 Triple 3-Input NAND Gate

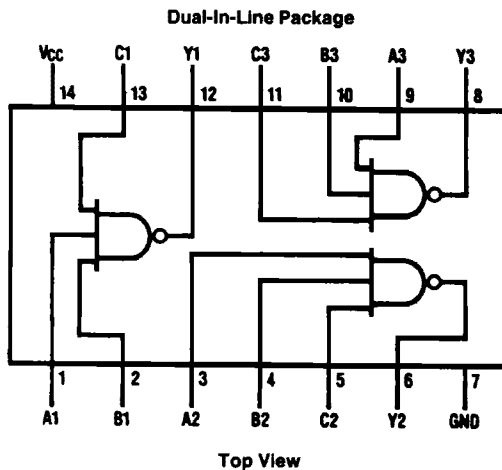
### General Description

These NAND gates utilize advanced silicon-gate CMOS technology to achieve operating speeds similar to LS-TTL gates with the low power consumption of standard CMOS integrated circuits. All gates have buffered outputs. All devices have high noise immunity and the ability to drive 10 LS-TTL loads. The 54HC/74HC logic family is functionally as well as pin-out compatible with the standard 54LS/74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to  $V_{CC}$  and ground.

### Features

- Typical propagation delay: 8 ns
- Wide power supply range: 2–6V
- Low quiescent current: 20  $\mu$ A maximum (74HC Series)
- Low input current: 1  $\mu$ A maximum
- Fanout of 10 LS-TTL loads

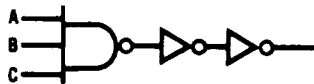
### Connection and Logic Diagrams



TL/F/5153-1

Order Number MM54HC10\* or MM74HC10\*

\*Please look into Section 8, Appendix D for availability of various package types.



$$Y = \overline{ABC}$$

TL/F/5153-2

**Absolute Maximum Ratings** (Notes 1 & 2)

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage ( $V_{CC}$ )	-0.5 to +7.0V
DC Input Voltage ( $V_{IN}$ )	-1.5 to $V_{CC} + 1.5V$
DC Output Voltage ( $V_{OUT}$ )	-0.5 to $V_{CC} + 0.5V$
Clamp Diode Current ( $I_{IK}, I_{OK}$ )	$\pm 20$ mA
DC Output Current, per pin ( $I_{OUT}$ )	$\pm 25$ mA
DC $V_{CC}$ or GND Current, per pin ( $I_{CC}$ )	$\pm 50$ mA
Storage Temperature Range ( $T_{STG}$ )	-65°C to +150°C
Power Dissipation ( $P_D$ )	
(Note 3)	600 mW
S.O. Package only	500 mW
Lead Temperature ( $T_L$ )	
(Soldering 10 seconds)	260°C

**Operating Conditions**

	Min	Max	Units
Supply Voltage ( $V_{CC}$ )	2	6	V
DC Input or Output Voltage ( $V_{IN}, V_{OUT}$ )	0	$V_{CC}$	V
Operating Temp. Range ( $T_A$ )			
MM74HC	-40	+85	°C
MM54HC	-55	+125	°C
Input Rise or Fall Times ( $t_r, t_f$ )			
$V_{CC} = 2.0V$		1000	ns
$V_{CC} = 4.5V$		500	ns
$V_{CC} = 6.0V$		400	ns

**DC Electrical Characteristics** (Note 4)

Symbol	Parameter	Conditions	$V_{CC}$	$T_A = 25^\circ C$		74HC $T_A = -40$ to $85^\circ C$		54HC $T_A = -55$ to $125^\circ C$		Units	
				Typ	Guaranteed Limits						
$V_{IH}$	Minimum High Level Input Voltage		2.0V		1.5	1.5	1.5		V		
			4.5V		3.15	3.15	3.15		V		
			6.0V		4.2	4.2	4.2		V		
$V_{IL}$	Maximum Low Level Input Voltage**		2.0V		0.5	0.5	0.5		V		
			4.5V		1.35	1.35	1.35		V		
			6.0V		1.8	1.8	1.8		V		
$V_{OH}$	Minimum High Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 20 \mu A$	2.0V	2.0	1.9	1.9	1.9		V		
			4.5V	4.5	4.4	4.4	4.4		V		
			6.0V	6.0	5.9	5.9	5.9		V		
		$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 4.0$ mA $ I_{OUT}  \leq 5.2$ mA	4.5V	4.2	3.98	3.84	3.7		V		
			6.0V	5.7	5.48	5.34	5.2		V		
$V_{OL}$	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ $ I_{OUT}  \leq 20 \mu A$	2.0V	0	0.1	0.1	0.1		V		
			4.5V	0	0.1	0.1	0.1		V		
			6.0V	0	0.1	0.1	0.1		V		
		$V_{IN} = V_{IH}$ $ I_{OUT}  \leq 4.0$ mA $ I_{OUT}  \leq 5.2$ mA	4.5V	0.2	0.26	0.33	0.4		V		
			6.0V	0.2	0.26	0.33	0.4		V		
$I_{IN}$	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		$\pm 0.1$	$\pm 1.0$	$\pm 1.0$	$\mu A$			
$I_{CC}$	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		2.0	20	40	$\mu A$			

**Note 1:** Absolute Maximum Ratings are those values beyond which damage to the device may occur.

**Note 2:** Unless otherwise specified all voltages are referenced to ground.

**Note 3:** Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

**Note 4:** For a power supply of 5V  $\pm 10\%$  the worst case output voltages ( $V_{OH}$  and  $V_{OL}$ ) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case  $V_{IH}$  and  $V_{IL}$  occur at  $V_{CC} = 5.5V$  and 4.5V respectively. (The  $V_{IH}$  value at 5.5V is 3.85V.) The worst case leakage current ( $I_{IN}$ ,  $I_{CC}$ , and  $I_{OZ}$ ) occur for CMOS at the higher voltage and so the 6.0V values should be used.

\*\* $V_{IL}$  limits are currently tested at 20% of  $V_{CC}$ . The above  $V_{IL}$  specification (30% of  $V_{CC}$ ) will be implemented no later than Q1, CY'89.

**AC Electrical Characteristics**  $V_{CC}=5V$ ,  $T_A=25^\circ C$ ,  $C_L=15\text{ pF}$ ,  $t_r=t_f=6\text{ ns}$ 

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
$t_{PHL}$ , $t_{PLH}$	Maximum Propagation Delay		8	15	ns

**AC Electrical Characteristics**  $V_{CC}=2.0V$  to  $6.0V$ ,  $C_L=50\text{ pF}$ ,  $t_r=t_f=6\text{ ns}$  (unless otherwise specified)

Symbol	Parameter	Conditions	$V_{CC}$	$T_A=25^\circ C$		74HC	54HC	Units
						$T_A=-40$ to $85^\circ C$	$T_A=-55$ to $125^\circ C$	
				Typ	Guaranteed Limits			
$t_{PHL}$ , $t_{PLH}$	Maximum Propagation Delay		2.0V	48	90	113	134	ns
			4.5V	10	18	23	27	ns
			6.0V	8	15	19	23	ns
$t_{TLH}$ , $t_{THL}$	Maximum Output Rise and Fall Time		2.0V	30	75	95	110	ns
			4.5V	8	15	19	22	ns
			6.0V	7	13	16	19	ns
$C_{PD}$	Power Dissipation Capacitance (Note 5)	(per gate)		20				pF
$C_{IN}$	Maximum Input Capacitance			5	10	10	10	pF

**Note 5:**  $C_{PD}$  determines the no load dynamic power consumption,  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ , and the no load dynamic current consumption,  $I_S = C_{PD} V_{CC} f + I_{CC}$ .